TO-92 Plastic-Encapsulate Transistors

2N5088 TRANSISTOR（ NPN ）

FEATURES

Power dissipation

P_{CM}： 0.625 W（Tamb=25℃）

Collector current

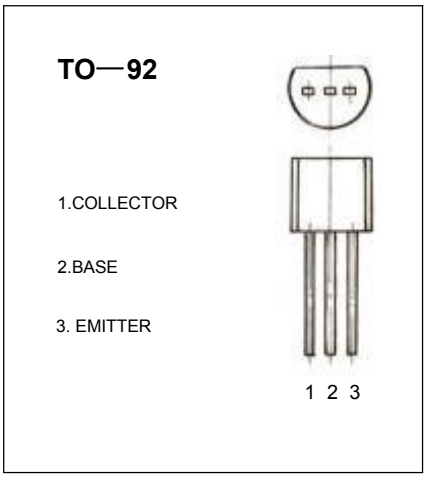
I_{CM}： 0.1 A

Collector-base voltage

$V_{(BR)CBO}$: 35 V

Operating and storage junction temperature range

T_J，T_{stg}: -55℃ to +150℃



ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	I_C=100μA, I_E=0	35			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C=1mA，I_B=0	30			V
Collector cut-off current	I_{CBO}	V_{CB}=20V , I_E=0			50	μA
Emitter cut-off current	I_{EBO}	V_{EB}=3V，I_C=0			50	μA
DC current gain	H_{FE}（1）	V_{CE}=5V, I_C=100μA	300		900	
DC current gain	H_{FE}（2）	V_{CE}=5V, I_C=1mA	350			
DC current gain	H_{FE}（3）	V_{CE}=5V, I_C=10mA	300			
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=10mA, I_B=1mA			0.5	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=10mA,V_{CE}=5V			0.8	V
Transition frequency	f_T	V_{CE}=5V, I_C=500μA f=20MHz	50			MHz

CLASSIFICATION OF HFE

Rank	1	2	3
Range	300-500	500-600	600-900